Fuel retention properties in first wall materials: the influence of displacement damage, microstructure, and helium

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WP PFC, WP PWIE, WP MAT-IREMEV





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Fuel retention properties in tungsten: the influence of displacement damage, microstructure, and helium

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- Introduction / Motivation
- Deuterium retention in W-irradiated W and the effect of:
 - annealing
 - D presence
 - defects on D location in the tungsten
 - He in the bulk and at the surface
 - Influence of microstructure grain boundaries
- Conclusion





Simplified plasma-wall interaction

Tungsten – plasma facing material – first wall and divertor



Last ten years the focus was on displacement damage

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Hydrogen interaction picture (kinetics and dynamics): energy potential





Hydrogen interaction picture (kinetics and dynamics): energy potential



Hydrogen interaction picture (kinetics and dynamics): energy potential diagram



Separating individual aspects of the interaction





Damaged layer characterization by Scanning Transmission Electron Microscopy (STEM) [Založnik et al. Phys Scr. T167 (2016) 014031]

W ion irradiation by MeV W ions

- Creation of displacement damage
- Dense cascades

He irradiations (bulk and surface) later

- Exposure to D atoms/ions to only populate the existing traps without producing new ones
- Open volume defects are traps for hydrogen isotopes [S. M. Myers et al., JNM 165 (1989) 9– 64]

Methodology to quantify D retention, defect evolution and defect concentration:

- measure D concentration by nuclear reaction analysis (NRA) via D(³He,p)⁴He
- desorption kinetics by thermal desorption spectroscopy (TDS)
- Use macroscopic rate equation modelling

• How to obtain defect densities and de-trapping energies



Determination of defect density and de-trapping energies: Fitting D depth profile and TDS spectrum by rate equation modelling codes (MHIMS, TESSIM)

300 eV D exposure at 450 K

- ✓ Double peak
- ✓ Five de-trapping energies 1.35 eV 2.09 eV
- 0.3 eV D exposure at 600 K
- ✓ Single peak
- ✓ 3x lower D amount
- Active thermal detrapping!
- ✓ Three de-trapping energies





Creation of displacement damage: dpa dependence at 290 K



> Deuterium concentration as a function of damage dose (irradiation @ 290 K).



No displacement damage – D concentration 10⁻³ at. % Small dpa < 0.03 – isolated defects, linear dependence on damage dose

High dpa > 0.1 – cascade overlap -> saturation of D concentration @ 1 at. %

Saturation of defect density 1 at. %



[T. Schwarz-Selinger, Mater. Res. Express 10 (2023) 102002]

Dpa dependence at elevated temperatures? Talk by M. Zibrov All further studies in damage saturation > 0.1 dpa

Defect evolution with temperature: post annealing



Damaging at room temperature and post-annealing:

- Vacancy migration above 500 K [Keys and Moteff JNM 34 (1970) 260; A. Debelle et al., 376 (2008) 216-221]
- Cluster migration, annihilation and coalescence at higher temperature
- Reduction of dislocation lines and loops
 [F. Ferroni et al., Acta Mater. 90 (2015) 380–93]
- Reduction of D concentration reduction in defect density.
- ✓ A complete recovery appears only above 2000 K
- Cluster migration, annihilation and coalescence slight suppression due to presence of D Pecovnik et al. Nucl. Fusion 60 (2020) 106028



- O.V. Ogorodnikova et al., J. Nucl. Mater. 451 (2014) 379-86.
- E. Markina J. Nucl. Mater. 463 (2015) 329–32.
- A. Založnik, Phys. Scripta T167 (2016) 014031.
- M. Zibrov et al. NME 23 (2020) 100747

concentration (%)

Vormalized D max.

W irradiation at elevated temperatures + sequential exposure to D



Damaging at high temp. (sequential) + 300 eV D exposure at 450 K

- D concentration decreases with irradiation temperature
- Less defects created at elevated temperatures



Defect evolution with temperature: irradiation at high temperatures versus post-annealing



Damaging at high temp. (sequential) + 300 eV D exposure at 450 K

- D concentration decreases with irradiation temperature
- Less defects created at elevated temperatures

Damaging at 300 K and post-annealing + D @ 400 K

Defects anneal with increase of temperature



Nearly 50 % less traps compared to post-annealing

⇒ Speculation: Annealing of an evolving defect structure compared to annealing of large scale defects

W irradiation at elevated temperatures with D + sequential exposure to D



- Increase of D concentration (factor of two) larger defect concentration due to presence of D
- Higher defect densities at low temperatures

ion flux?

10 MeV W ions

 \geq

- Reduced defect stabilization at high temperatures due to thermal detrapping of D during experiment for our D ion fluxes
- \blacktriangleright Increase of stabilization at T \geq 1000 ? ongoing study
- Rate equation modelling to understand the observed phanomena Model on defect stabilization due to trapping of D in defects [Pečovnik et al. Nucl. Fusion 60 (2020) 036024]
- First MD modelling that reproduces experimental observations [Lindbland, Mason and Granberg 2024] https://dx.doi.org/10.2139/ssrn.4808177]



T_{exp} [K]

800

900

700

Undamaged

600

500

400

0.0 -

300

S. Markelj et al., Nuclear Fusion 59 (2019) 086050.

1000 1100 1200



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Influence of D presence on defect creation in W





Schwarz-Selinger et al. NME 17, 228–234 (2018).

- Application of the *defect stabilization model* to different experiment
- D saturation concentration at 4.2 at.% is expected
- M. Pečovnik et al., J. Nucl. Mater. 550, 152947 (2021)



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Summary on the defect densities and D trapping energies



All in all, 8 detrapping energies found – the same in all studies cases

2.0

[eV]

energy

Exp. Sim

n, = 0.05 at. E = 2.05 eV

Defect densities change with temperature and exposure scenario (sequential / simultaneous)

n. = 0.22 at.%

D/m²s]

flux [10¹⁸]

S 0.2

E = 1.08, 1.16, 1.25, 1.34, 1.46 eV

Three defect types with several fill-levels:

```
Defect type 1 - (1.08, 1.16, 1.25, 1.34, 1.46) eV;
```

Defect type 2 – (1.68, 1.86) eV;

Defect type 3 - 2.05 eV.

Δ

- Comparison to DFT calculations
 - Defect 1 -> single vacancies
 - Defect 2 -> small vacancy clusters



n, = 0.29 at.%

E = 1.68, 1.86 eV

of trapped HI

The "Physicist" approach (Hodille et al.)



Take the concentration of the vacancy cluster Vn from the MD simulations (AT-ZN potential) of cumulative cascade up to 0.2 dpa [*F. Granberg et al. JNM 556 (2021) 153158*]



Detrapping energies for VnHk obtained with the model derived from DFT calculations [J. Hou et al. Nature materials, 18 (2019) 833–839].





• Agreement acceptable

Hodille et al. PSI proceedings, submitted to NME 2024 Study preformed under EUROfusion Enabling research project **DeHydroC** S. Markelj, IAEA AMPMI 2024 | Page 18



- Method to determine hydrogen interstitial sites in metals in 70's/80's
- [Fukai, The metal-hydrogen systems, Springer 2005]
- Examples of detection of hydrogen in metals by NRA-channeling by group of Picraux and Myers in Sandia National Laboratories (SNL), New Mexico; Implantation by keV D ions!



Angular scans through the <100> axis on W ➤ Deuterium sitting in tetrahedral sites

Picraux, S. T. & Vook, F. L. Deuterium lattice location in Cr and W. Phys. Rev. Letters 33, 1216 (1974).



But:

- Academic case of defect free(?) tungsten
- > Only qualitative measurement
- 30 keV D ions created vacancies by themselves, even possible to determined position of solute atoms, signal should be dominated by trapped D!





Incorporation of NRA-C into binary collision approximation code RBSADEC

[Zhang, S. et al. Physical Review E 94, (2016)]

• RBS-C: a pristine W target



0.1 % of D at tetrahedral sites





 $3 imes 10^{15}$ cm⁻² 30 keV D on W

Difference between experiments and simulations: not exactly on tetrahedral sites?

- Hydrogen in vacancies, some position close to tetrahedral sites, etc.
- Effect of damage dose: D sites change
- Improving the fit: adjust D locations,
 - D location according to DFT calculations S. Markelj, IAEA AMPMI 2024 | Page 20

Study preformed under EUROfusion Enabling research project **DeHydroC**

Development of C-NRA simulation and detection of D by RBSADEC code



 SRIM calculation of vacancy distribution for 30 keV D ions in W for Picraux experiment

(S. Picraux, Phys. Rev. Lett., 33, 1974)



Multiple hydrogen occupancy in a

Fernandez et al. Acta Materialia (2015)]

vacancy [Heinola et al. PR B (2010),

 Calculation the NRA and RBS yield



Best agreement obtained for He-field vacancy with 5 H atoms



[Jin et al. Phys. Rev. Materials 8, 043604 (2024)]

DeHydroC

Creation of vacancies

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Effort to detect D location in W in defects





W (100) single crystal should show a difference in the C-NRA signal when D is near the octahedral (OIS) or tetrahedral interstitial sites (TIS) [Cabstanjen, H.-D. Phys. Stat. Sol. (a) 59, 11-26 (1980)].



Markelj et al. NME 39 (2024) 101630 Markelj et al. Acta Materiallia 263 (2024) 119499

Diff. sizes Vn=25 and V_2 and 50 @ low dose

Based on Hu et al. JNM 556 (2022) 153175 – open volume type defects

Sample	Irradiation conditions	Predominant defect expected
78g / #1	0.02 dpa, 290 K	single vacancies
78f / #5	0.2 dpa, 290K	heavily damaged standard
78c / #3	0.02 dpa, 800 K	small vacancy clusters
78b / #2	0.2 dpa, 800 K	big vacancy clusters

• NRA-C and RBS-C: DeHydroC first measurements



³He 0.8 MeV – simultaneous RBS-C and NRA-C 2D maps

2D map for sample #2: 800 K, 0.2 dpa

0.1

-3.5

е, о, з





RBS-C was performed at the Hedgehog setup for RBS channeling at Ion Beam Center at HZDR.

DeHydroC



Markelj et al. NME 39 (2024) 101630

-2.9 -2.5 -2.1 -1.7 -1.2 -0.8 -0.4 -0.0 0.4 0.8 1.2 1.7 2.1 2.5 2.9 Theta (°)

NRA-C

3,75

3,50

3,25

3,00

2,75

2,50

2,25

2,00

1,75

1,50

1,25

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NRA-C and RBS-C: angular scans



³He 0.8 MeV – simultaneous RBS-C and NRA-C 2D maps



- The NRA signal peak for the samples irradiated at 800 K has a <u>wider and higher NRA signal compared</u> to the 0.02 dpa/290 l[´]
- Speculation: vacancy broader distribution,

DeHydroC

Work ongoing: NRA-C simulations, combination with DFT - multi occupancy of H in vacancy and vacancy clusters

ese clusters has a

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Different sources of He in fusion device





M.J. Baldwin et al. NF 51 (2011) 103021

Influence of He on surface ?

Affects the tungsten surface by bubble growth – decrease deuterium/tritium uptake into bulk and retention [Baldwin et al. NF 51 (2011) 103021]

distorted surface





Effect of different He fluences/concentrations on D retention







- Observed change of D retention for different He concentrations
- Increase of D concentration:
 - ➢ By 1.4 1% He
 - ➢ By 2.5 3.4% He
 - ➢ By 2.9 6.8% He
- No influence of He on D transport in the bulk



Markelj et al. Nucl. Fusion 60 (2020) 106029

Effect of different bulk He concentrations on D retention





 In the main wall of a future fusion device the effect of He will not dominate D retention in W since the expected He concentrations in DEMO of ~700 appm are well bellow 1 at. % = 10000 appm

Effect of post-annealing with He on D retention





He bubbles do not act as transport-barrier

Markelj et al. Nucl. Fusion 60 (2020) 106029 S. Markelj, IAEA AMPMI 2024 | Page 29

1.5

Depth [µm]

2.0

2.5

3.0

1.0

0.5

0.0

D uptake in He-containing W: NRA



> Self-damaged W as 'getter' underneath the He-implantation zone

- For the same fluence D hardly penetrates beyond He implantation zone
 - → $D_{max} \approx 8 \text{ at.}\%!$
- > Nearly unaffected by He fluence
- Nearly unaffected by He exposure temperature
- Decreased deuterium uptake surface effect Increased recycling due to 'open porosity'?
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Markelj et al. unpublished



The influence of grain boundaries on displacement damage and D retention





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We studied samples with:

size (80 nm)

Nanometer grain size (25 nm)

Hundreed nanometer grain

Micrometer grain size $(1 \mu m)$

Influence of grain size on D retention and transport



45



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35

40

Influence of grain size on D transport







Nanocrystalline structure

Influence of grain boundaries (GB) on hydrogen isotope transport

- E_{dif-lat} = 0.28 eV [Holzner et al., Phys. Scr. T171 (2020) 014034]
- GB in polycrystalline W can provide fast and extended transport channel [Toussaint Phys. Scr. T159 (2014) 014058] - depending on the grain.
 - E_{dif-GB} = 0.13 eV [Zhou et al., NF 50 (2010) 025016]
- GB can also be trapping sites for hydrogen isotopes [Oda, FED 112 (2016) 102]
 - E_{bind-GB}= 1.1 eV [Zhou et al., NF 50 (2010) 025016]
- Even though D diffuses along the grain boundaries, D goes back into the grains and populates the defects within the grains
- GB affect ion and atom transport Property of the bulk change of E_{dif} in bulk





- Need for microscopic understanding of the influence of defects on hydrogen isotope retention and vice versa – our approach to separate the defect creation and the effect of D and defects decoration by D
- The effect of D presence on damage creation:
- > D presence increases damage creation by more than a factor of 2
- De-trapping energies do not change
- He in the bulk and on the surface:
- He presence at the surface and in the bulk: locally He atoms/clusters/bubbles act as additional traps for deuterium (He/D = 3). D is preferentially retained were the He sits.
- He close to the surface increases locally D retention but leads to a significantly <u>reduced</u> <u>uptake into depth</u> by a factor up to 15.
- Grain boundaries
- ➢ Influence on the D transport faster diffusion along the grain boundaries





Open questions:

- Lacking a model on defect annealing do defects anneal / change during TDS
- Effect of D ion flux on defect creation and evolution at high temperatures
- Hydrogen isotope trapping at different defects which responsible for fuel retention, do we really know?
- D location around vacancies or vacancy clusters Very first NRA-C measurements on irradiated W samples with different defect structures show clear difference in the NRA-C response (EUROfusion DeHydroC project)
 - Modelling is necessary to understand NRA-C experimental results
- Only experiment with modelling hand in hand can bring progress in the field



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Thank you for your attention

Nanocrystalline samples – grain size





Influence of grain size on D retention





- Lower D concentration for largest grain size sample -similar to recrystallized W
- > Nanocrystalline material larger D retention undamaged

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In agreement with [Ogorodnikova, J. Appl. Phys. 122,

044902 (2017)]

D ion exposure – D depth profiles

Influence of grain size on D retention

300 eV D ions exposure at 450 K to exposure time sufficient to fill the damaged layer:

- <u>Saturation of D concentration at</u> ~1.5 at. % in damaged zone
- Similar D concentration for nano and hundred nm grain size
- Lower D concentration for largest grain size sample – but not drastic (similar to W reference)
- <u>Larger D concentration at the</u> interface – oxides, defects?





